



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: **IRINO, Kiyoshi**

Group Art Unit: **2815**

Serial No.: **09/428,052**

Examiner: **DIAZ, Jose R.**

Filed: **October 27, 1999**

Conformation No.: **4139**

For: **METHOD OF FABRICATING A SEMICONDUCTOR DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM**

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Date: December 8, 2003

Sir:

Prior to continued examination, please amend the above-identified application as follows:

